



STAP85035

RF power transistor, LdmoST plastic family
N-channel enhancement-mode lateral MOSFETs

Features

- Excellent thermal stability
- Common source configuration
- $P_{OUT} = 35\text{ W}$ with 14.9 dB gain @ 870 MHz / 13.6 V
- Plastic package
- ESD protection
- In compliance with the 2002/95/EC European directive

Description

The STAP85035 is a common source N-channel, enhancement-mode lateral field-effect RF power transistor. It is designed for high gain, broadband commercial and industrial applications. It operates at 13.6 V in common source mode at frequencies of up to 1 GHz. STAP85035 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in STAP ST Advanced PowerSO-10RF package. STAP85035's superior linearity performance makes it an ideal solution for car mobile radio. The STAP plastic package was designed to offer high reliability and high power capability. It has been specially optimized for RF needs and offers excellent RF performances and ease of assembly.

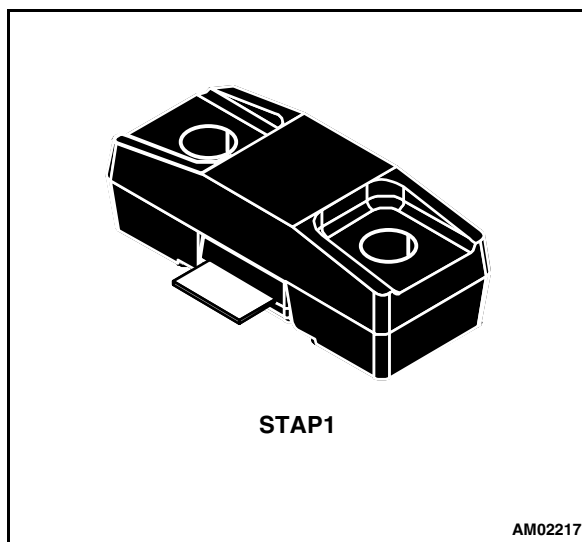
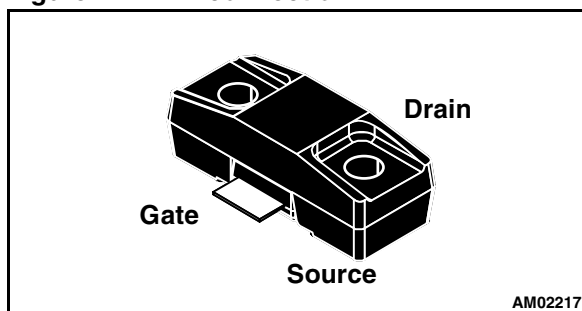


Figure 1. Pin connection



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1 Electrical data

1.1 Maximum ratings

Table 2. Absolute maximum ratings ($T_{CASE} = 25\text{ °C}$)

| Symbol | Parameter | Value | Unit |
|---------------|---|-------------|------|
| $V_{(BR)DSS}$ | Drain-source voltage | 40 | V |
| V_{GS} | Gate-source voltage | -0.5 to +15 | V |
| I_D | Drain current | 8 | A |
| P_{DISS} | Power dissipation (@ $T_C = 70\text{ °C}$) | 95 | W |
| T_J | Max. operating junction temperature | 165 | °C |
| T_{STG} | Storage temperature | -65 to +150 | °C |

1.2 Thermal data

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|------------|------------------------------------|-------|------|
| R_{thJC} | Junction - case thermal resistance | 1.0 | °C/W |

2 Electrical characteristics

$$T_{\text{CASE}} = +25\text{ }^{\circ}\text{C}$$

2.1 Static

Table 4. Static

| Symbol | Test conditions | | Min | Typ | Max | Unit |
|---------------------|--------------------------------|---------------------------------|-----|------|-----|---------------|
| I_{DSS} | $V_{\text{GS}} = 0\text{ V}$ | $V_{\text{DS}} = 25\text{ V}$ | | | 1 | μA |
| I_{GSS} | $V_{\text{GS}} = 5\text{ V}$ | $V_{\text{DS}} = 0\text{ V}$ | | | 1 | μA |
| V_{TH} | $I_{\text{D}} = 250\text{ mA}$ | | 2 | | 5 | V |
| $V_{\text{DS(ON)}}$ | $V_{\text{GS}} = 10\text{ V}$ | $I_{\text{D}} = 3\text{ A}$ | | 0.64 | 0.7 | V |
| C_{ISS} | $V_{\text{GS}} = 0\text{ V}$ | $V_{\text{DS}} = 12.5\text{ V}$ | | 76 | | pF |
| C_{OSS} | $V_{\text{GS}} = 0\text{ V}$ | $V_{\text{DS}} = 12.5\text{ V}$ | | 45 | | pF |
| C_{RSS} | $V_{\text{GS}} = 0\text{ V}$ | $V_{\text{DS}} = 12.5\text{ V}$ | | 1.4 | | pF |

2.2 Dynamic

Table 5. Dynamic

| Symbol | Test conditions | Min | Typ | Max | Unit |
|----------------|---|------|-----|-----|------|
| P3dB | $V_{\text{DD}} = 13.6\text{ V}$, $I_{\text{DQ}} = 350\text{ mA}$ $f = 870\text{ MHz}$ | 35 | 40 | - | W |
| G_{P} | $V_{\text{DD}} = 13.6\text{ V}$, $I_{\text{DQ}} = 350\text{ mA}$, $P_{\text{OUT}} = 15\text{ W}$, $f = 870\text{ MHz}$ | 15 | 17 | | dB |
| h_{D} | $V_{\text{DD}} = 13.6\text{ V}$, $I_{\text{DQ}} = 350\text{ mA}$, $P_{\text{OUT}} = P_{\text{3dB}}$, $f = 870\text{ MHz}$ | 60 | 72 | | % |
| Load mismatch | $V_{\text{DD}} = 17\text{ V}$, $I_{\text{DQ}} = 350\text{ mA}$, $P_{\text{OUT}} = 50\text{ W}$, $f = 870\text{ MHz}$ All phase angles | 20:1 | | | VSWR |

2.3 ESD protection characteristics

Table 6. ESD protection characteristics

| Test conditions | Class |
|------------------|-------|
| Human body model | 2 |
| Machine model | M3 |

3 Impedance

Figure 2. Current conventions

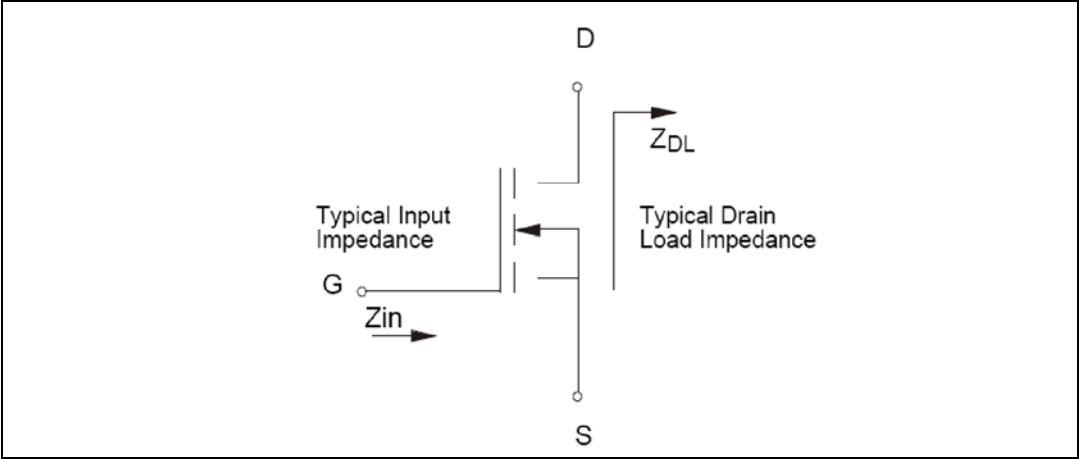


Table 7. Impedance data

| Frequency (MHz) | $Z_{IN} (\Omega)$ | $Z_{DL} (\Omega)$ |
|-----------------|-------------------|-------------------|
| 870 MHz | $0.57 + j\ 0.73$ | $1.73 - j\ 0.15$ |

4 Typical performances

Figure 3. Threshold voltage

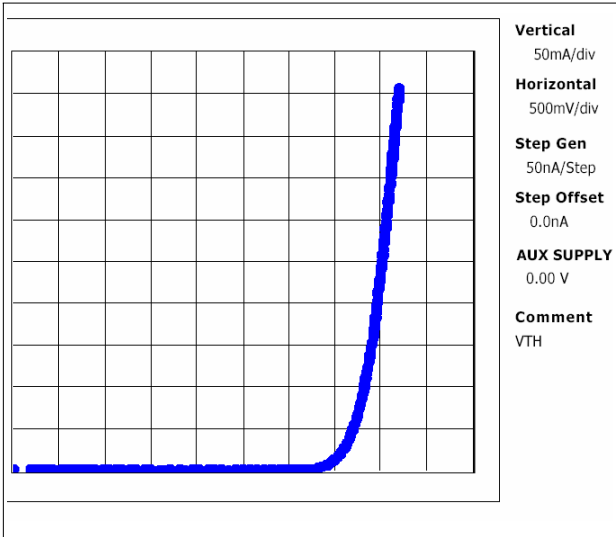


Figure 4. DC output characteristic

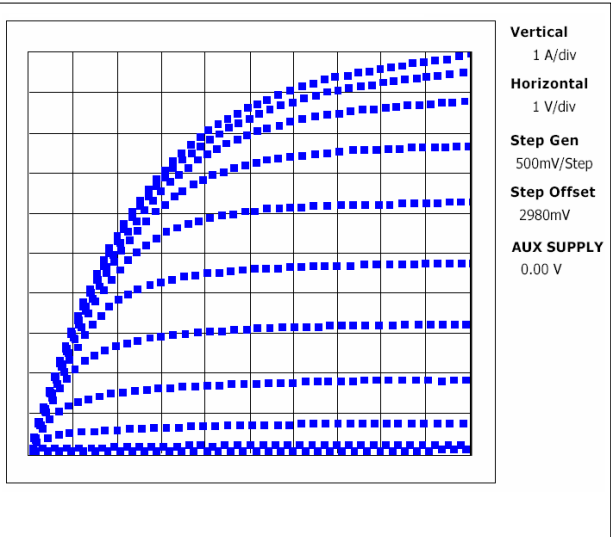


Figure 5. I_D vs V_{GS}

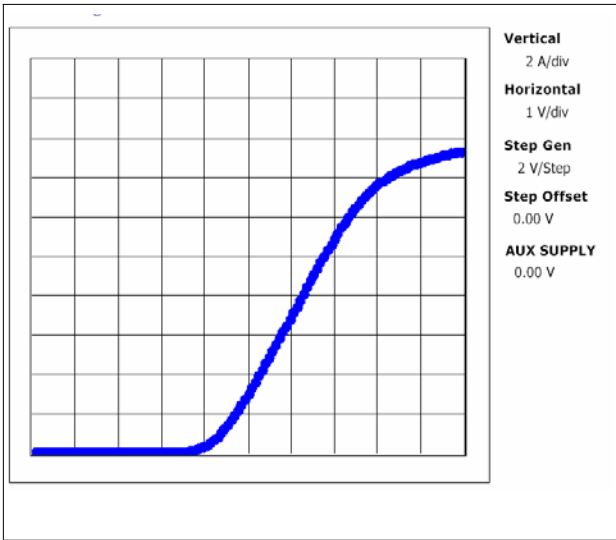


Figure 6. Capacitances vs voltage

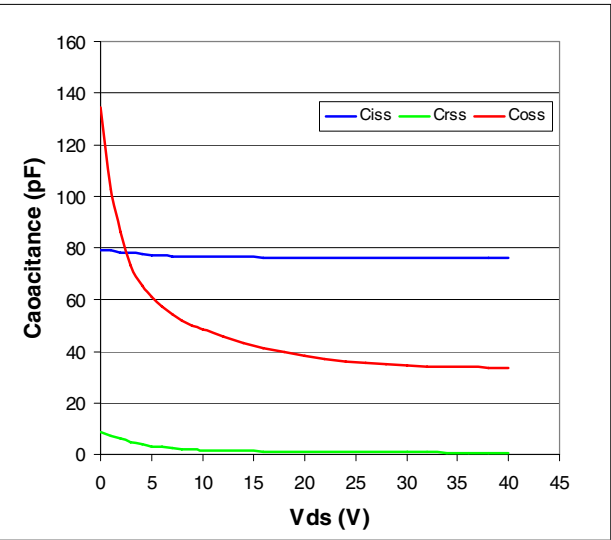


Figure 7. Pout and Id vs VGS

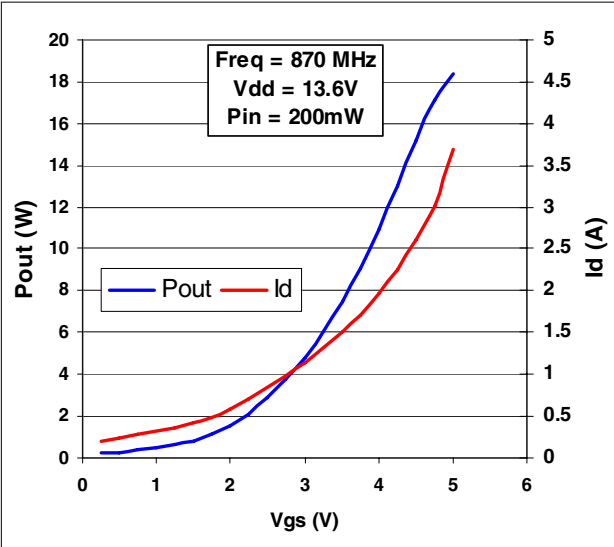


Figure 8. Pout and Id vs VGS

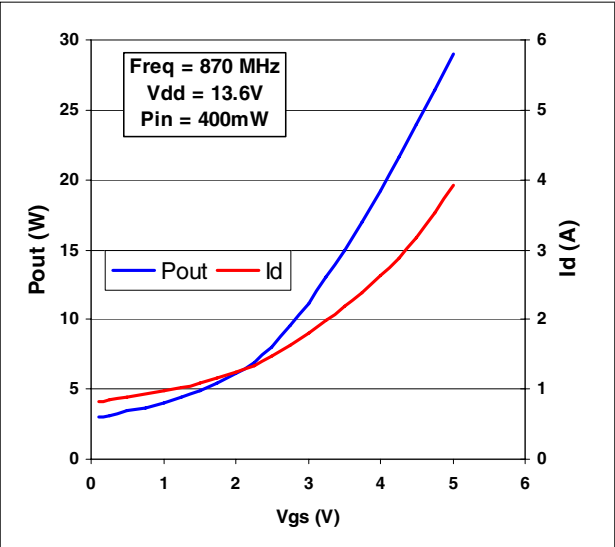


Figure 9. Gain vs Pout and bias current

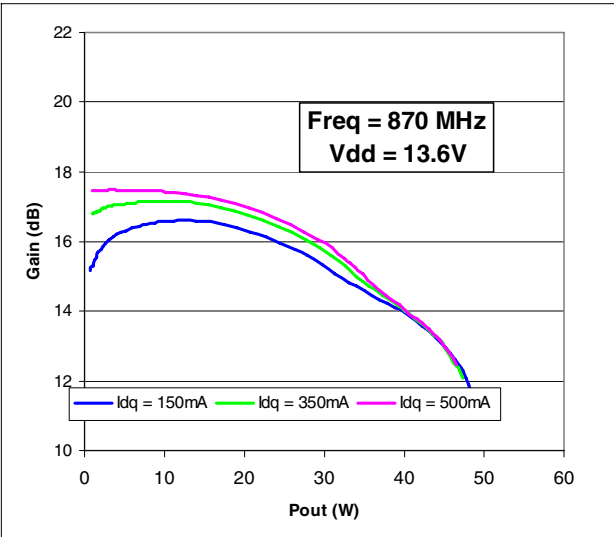


Figure 10. Gain and efficiency vs Pout

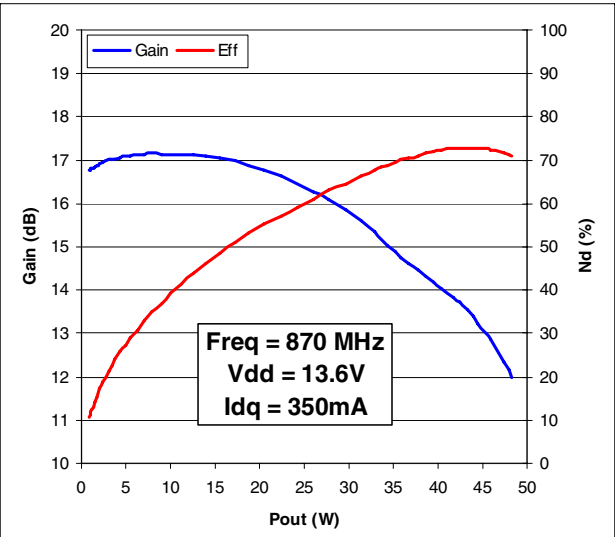


Figure 11. Pout and Id vs supply voltage

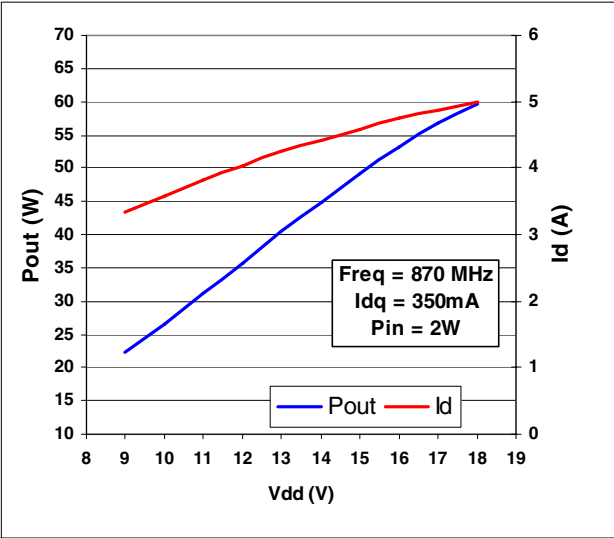
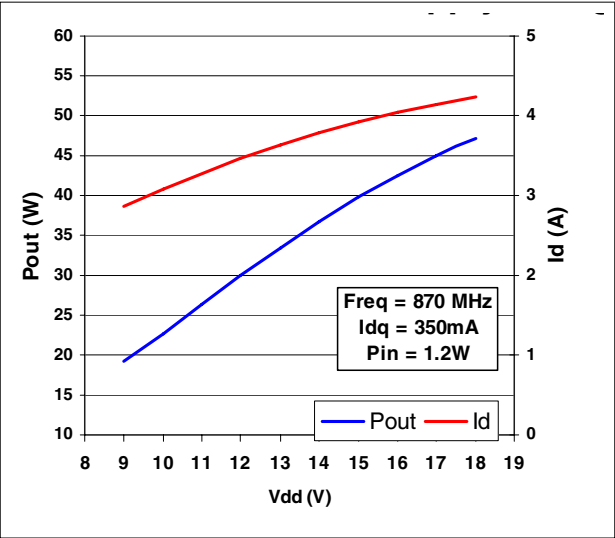


Figure 12. Pout and Id vs supply voltage



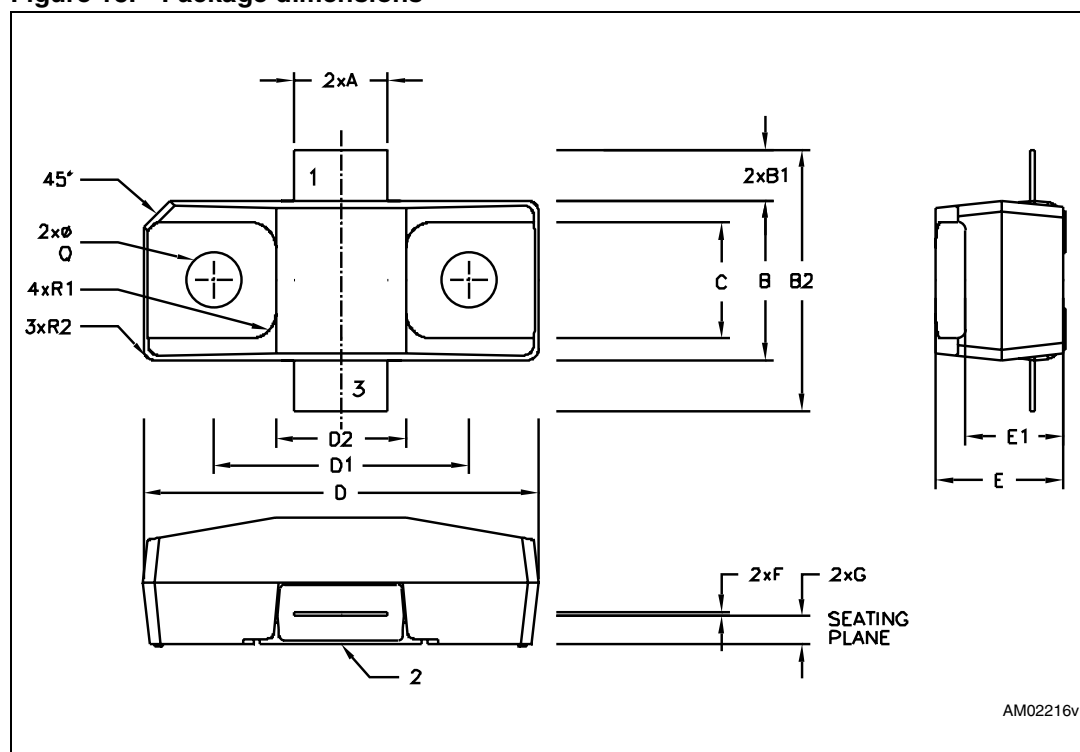
5 ECOPACK®

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Table 8. STAP1 mechanical data

| Dim. | mm. | | Inch | |
|------|-------|-------|-------|-------|
| | Min | Max | Min | Max |
| A | 5.40 | 5.65 | 0.212 | 0.222 |
| B | 9.27 | 9.53 | 0.365 | 0.375 |
| B1 | 2.90 | 3.10 | 0.114 | 0.122 |
| B2 | 15.10 | 15.65 | 0.594 | 0.616 |
| C | 6.60 | 6.99 | 0.260 | 0.275 |
| D | 23.11 | 23.42 | 0.910 | 0.922 |
| D1 | 14.88 | 15.19 | 0.586 | 0.598 |
| D2 | 7.52 | 7.82 | 0.296 | 0.308 |
| E | 7.42 | 7.57 | 0.292 | 0.298 |
| E1 | 5.69 | 5.84 | 0.224 | 0.230 |
| F | 0.21 | 0.31 | 0.008 | 0.012 |
| G | 1.62 | 1.72 | 0.064 | 0.068 |
| Q | 3.15 | 3.30 | 0.124 | 0.130 |
| R1 | 1.52 | | 0.060 | |
| R2 | 0.64 | | 0.025 | |

Figure 13. Package dimensions



6 Revision history

Table 9. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 01-Apr-2009 | 1 | Initial release |
| 07-Jul-2009 | 2 | Deleted moisture sensitivity level table on page 4 |

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